V23990-P760-A-PM
V23990-P760-AY-PM

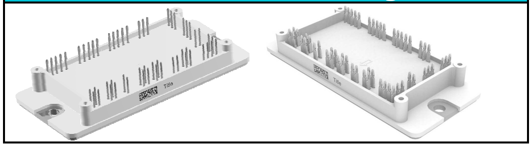
datasheet

flow **PIM 2 3rd** — **1200 V / 100 A**

Features

- 3~rectifier,BRC,Inverter, NTC
- Very Compact housing, easy to route
- IGBT4/ EmCon4 technology for low saturation losses and improved EMC behavior

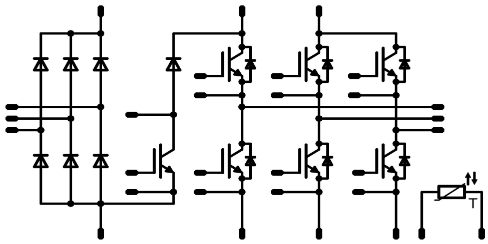
flow 2 17mm housing



Target Applications

- Motor Drives
- Power Generation

Schematic



Types

- V23990-P760-A-PM
- V23990-P760-AY-PM

Maximum Ratings

T_j=25°C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Input Rectifier Diode				
Repetitive peak reverse voltage	V_{RRM}		1600	V
Forward current	I_{FAV}	DC current — T_h=80°C T_c=80°C	100 100	A
Surge forward current	I_{FSM}	t_p=10ms — T_j=25°C	1000	A
I2t-value	I^2t		5000	A^2s
Power dissipation	P_{tot}	T_j=$T_j$max — T_h=80°C T_c=80°C	114 172	W
Maximum Junction Temperature	$T_j$max		150	°C
Inverter IGBT				
Collector-emitter break down voltage	V_{CE}		1200	V
DC collector current	I_C	T_j=$T_j$max — T_h=80°C T_c=80°C	105 120	A
Repetitive peak collector current	I_{Cpulse}	t_p limited by $T_j$max	300	A
Power dissipation	P_{tot}	T_j=$T_j$max — T_h=80°C T_c=80°C	263 398	W
Gate-emitter peak voltage	V_{GE}		±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j≤150°C V_{GE}=15V	10 800	μs V
Maximum Junction Temperature	$T_j$max		175	°C

Maximum Ratings

Tj=25°C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Inverter FWD					
Peak Repetitive Reverse Voltage	V_{RRM}			1200	V
DC forward current	I_F	$T_j=T_jmax$	$T_h=80°C$ $T_c=80°C$	86 114	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_jmax		200	A
Power dissipation	P_{tot}	$T_j=T_jmax$	$T_h=80°C$ $T_c=80°C$	150 230	W
Maximum Junction Temperature	T_jmax			175	°C
Brake IGBT					
Collector-emitter break down voltage	V_{CE}			1200	V
DC collector current	I_C	$T_j=T_jmax$	$T_h=80°C$ $T_c=80°C$	59 76	A
Repetitive peak collector current	I_{Cpuls}	t_p limited by T_jmax		150	A
Power dissipation	P_{tot}	$T_j=T_jmax$	$T_h=80°C$ $T_c=80°C$	159 241	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	$T_j≤150°C$ $V_{GE}=15V$		10 900	μs V
Maximum Junction Temperature	T_jmax			175	°C
Brake Inverse Diode					
Peak Repetitive Reverse Voltage	V_{RRM}			1200	V
DC forward current	I_F	$T_j=T_jmax$	$T_h=80°C$ $T_c=80°C$	20 20	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_jmax		20	A
Brake Inverse Diode	P_{tot}	$T_j=T_jmax$	$T_h=80°C$ $T_c=80°C$	52 79	W
Maximum Junction Temperature	T_jmax			175	°C
Brake FWD					
Peak Repetitive Reverse Voltage	V_{RRM}			1200	V
DC forward current	I_F	$T_j=T_jmax$	$T_h=80°C$ $T_c=80°C$	35 40	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_jmax		50	A
Power dissipation	P_{tot}	$T_j=T_jmax$	$T_h=80°C$ $T_c=80°C$	75 114	W
Maximum Junction Temperature	T_jmax			175	°C

Maximum Ratings

Tj=25°C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Thermal properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{op}		-40…+Tjmax-25	°C
Insulation properties				
Insulation voltage	V_{is}	t=1min	4000	V_{DC}
Creepage distance			min 12,7	mm
Clearance			min 12,7	mm

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Input Rectifier Diode										
Forward voltage	V_F				100	Tj=25°C Tj=125°C		1,18 1,16	1,9	V
Threshold voltage (for power loss calc. only)	V_{to}				100	Tj=25°C Tj=125°C		0,88 0,75		V
Slope resistance (for power loss calc. only)	r_t				100	Tj=25°C Tj=125°C		0,003 0,004		Ω
Reverse current	I_r			1500		Tj=25°C Tj=125°C			0,05 1,1	mA
Thermal resistance chip to heatsink	R_{thJH}	Thermal grease thickness≤50μm λ = 0,61						0,62		K/W
Thermal resistance chip to case	R_{thJC}							0,41		
Inverter IGBT										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$			0,0034	Tj=25°C Tj=150°C	5	5,8	6,5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		100	Tj=25°C Tj=150°C		1,9 2,34	2,5	V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	1200		Tj=25°C Tj=150°C			0,03	mA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25°C Tj=150°C			700	nA
Integrated Gate resistor	R_{gint}							2		Ω
Turn-on delay time	$t_{d(on)}$	Rgoff=4 Ω Rgon=4 Ω	±15	600	100	Tj=25°C Tj=150°C		126 130		ns
Rise time	t_r					Tj=25°C Tj=150°C		17 22		
Turn-off delay time	$t_{d(off)}$					Tj=25°C Tj=150°C		242 316		
Fall time	t_f					Tj=25°C Tj=150°C		63 115		
Turn-on energy loss per pulse	E_{on}					Tj=25°C Tj=150°C		4,07 6,64		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25°C Tj=150°C		5,22 8,71		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25°C		5540		pF
Output capacitance	C_{oss}							410		
Reverse transfer capacitance	C_{rss}							320		
Gate charge	Q_{Gate}		±15			Tj=25°C		580		nC
Thermal resistance chip to heatsink	R_{thJH}	Thermal grease thickness≤50μm λ = 0,61 W/m·K						0,36		K/W
Thermal resistance chip to case	R_{thJC}							0,24		
Coupled thermal resistance transistor-transist	$R_{thJHT-T}$							0,08		
Coupled thermal resistance diode-transistor	$R_{thJHD-T}$							0,08		
Inverter FWD										
Diode forward voltage	V_F				100	Tj=25°C Tj=150°C		1,83 1,86	2,4	V
Peak reverse recovery current	I_{RRM}	Rgon=4 Ω	±15	600	100	Tj=25°C Tj=150°C		167 191		A
Reverse recovery time	t_{rr}					Tj=25°C Tj=150°C		134 293		ns
Reverse recovered charge	Q_{rr}					Tj=25°C Tj=150°C		9,39 19,67		μC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25°C Tj=150°C		7887 3332		A/μs
Reverse recovered energy	Erec					Tj=25°C Tj=150°C		3,82 8,55		mWs
Thermal resistance chip to heatsink	R_{thJH}	Thermal grease thickness≤50μm λ = 0,61 W/m·K						0,63		K/W
Thermal resistance chip to case	R_{thJC}							0,41		
Coupled thermal resistance diode-diode	$R_{thJHD-D}$									
Coupled thermal resistance transistor-diode	$R_{thJHT-D}$							0,07		

Characteristic Values

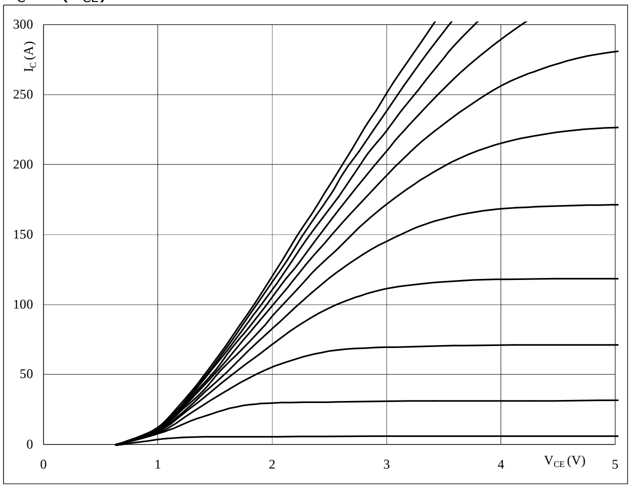
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Brake IGBT										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$			0,0017	Tj=25°C Tj=150°C	5	5,8	6,5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		50	Tj=25°C Tj=150°C		1,84 2,27	2,3	V
Collector-emitter cut-off incl diode	I_{CES}		0	1200		Tj=25°C Tj=150°C			0,25	mA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25°C Tj=150°C			700	nA
Integrated Gate resistor	R_{gint}							4		Ω
Turn-on delay time	$t_{d(on)}$	Rgoff=8 Ω Rgon=8 Ω	±15	600	50	Tj=25°C Tj=150°C		117 121		ns
Rise time	t_r					Tj=25°C Tj=150°C		18 24		
Turn-off delay time	$t_{d(off)}$					Tj=25°C Tj=150°C		249 316		
Fall time	t_f					Tj=25°C Tj=150°C		88 125		
Turn-on energy loss per pulse	E_{on}					Tj=25°C Tj=150°C		2,39 3,43		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25°C Tj=150°C		2,96 4,8		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25°C		2770		pF
Output capacitance	C_{oss}							205		
Reverse transfer capacitance	C_{rss}							160		
Gate charge	Q_{Gate}		±15	960		Tj=25°C		290		nC
Thermal resistance chip to heatsink	R_{thJH}	Thermal grease thickness≤50µm λ = 0,61 W/m·K						0,6		K/W
Thermal resistance chip to case	R_{thJC}							0,39		
Brake Inverse Diode										
Diode forward voltage	V_F				10	Tj=25°C Tj=150°C	1,1	1,84 1,8	2,1	V
Thermal resistance chip to heatsink	R_{thJH}	Thermal grease thickness≤50µm λ = 0,61 W/m·K						1,81		K/W
Thermal resistance chip to case	R_{thJC}							1,20		K/W
Brake FWD										
Diode forward voltage	V_F				25	Tj=25°C Tj=150°C		1,87 1,83	2,2	V
Reverse leakage current	I_r		±15	600	50	Tj=25°C Tj=150°C			10	µA
Peak reverse recovery current	I_{RRM}	Rgon=8 Ω	±15	600	50	Tj=25°C Tj=150°C		54,29 78,18		A
Reverse recovery time	t_{rr}					Tj=25°C Tj=150°C		158,7 295,4		ns
Reverse recovered charge	Q_{rr}					Tj=25°C Tj=150°C		3,21 6,6		µC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25°C Tj=150°C		4114 3412		A/µs
Reverse recovery energy	E_{rec}					Tj=25°C Tj=150°C		3,21 6,6		mWs
Thermal resistance chip to heatsink	R_{thJH}	Thermal grease thickness≤50µm λ = 0,61 W/m·K						1,27		K/W
Thermal resistance chip to case	R_{thJC}							0,84		
Thermistor										
Rated resistance	R_{25}	Tol. ±5%				Tj=25°C	20,9	22	23,1	kΩ
Deviation of R100	$D_{R/R}$	R100=1486.1Ω				Tc=100°C		2,9		%/K
Power dissipation given Epcos-Typ	P					Tj=25°C		210		mW
B-value	$B_{(25/100)}$	Tol. ±3%				Tj=25°C		4000		K

Output Inverter

Figure 1 Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



At

t_p = 250 µs

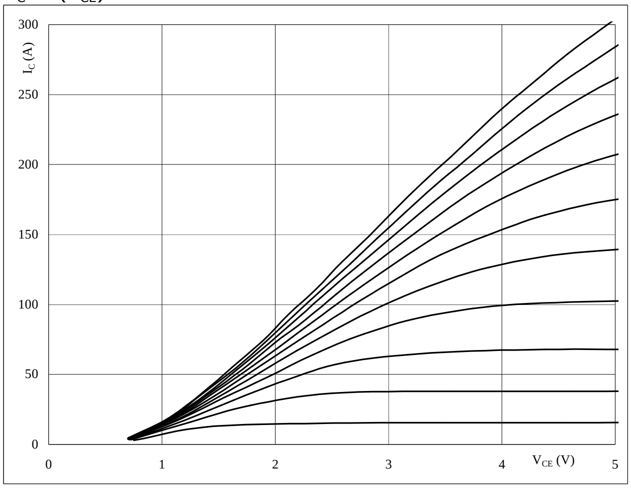
T_j = 25 °C

VGE from 7 V to 17 V in steps of 1 V

Figure 2 Output inverter IGBT

Typical output characteristics

$I_C = f(V_{CE})$



At

t_p = 250 µs

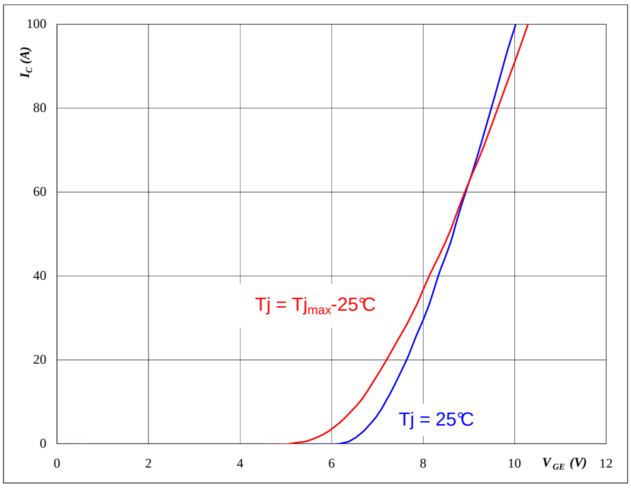
T_j = 150 °C

VGE from 7 V to 17 V in steps of 1 V

Figure 3 Output inverter IGBT

Typical transfer characteristics

$Ic = f(V_{GE})$



At

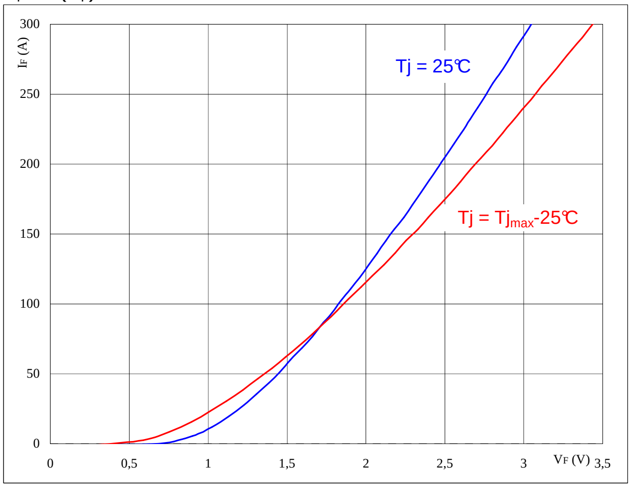
t_p = 250 µs

V_{CE} = 10 V

Figure 4 Output inverter FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

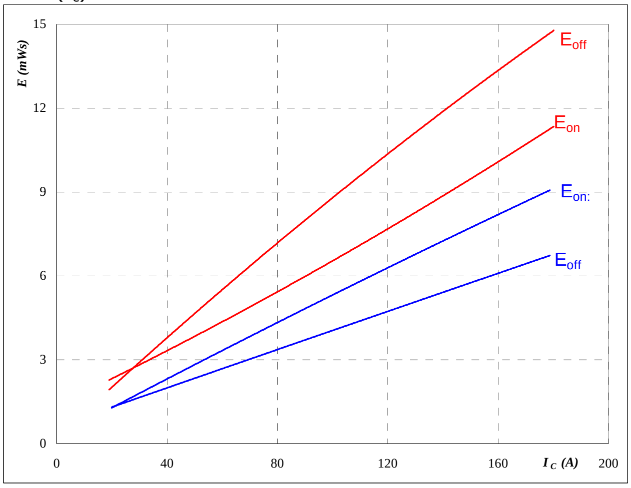
t_p = 250 µs

Output Inverter

Figure 5 Output inverter IGBT

Typical switching energy losses as a function of collector current

$E = f(I_c)$



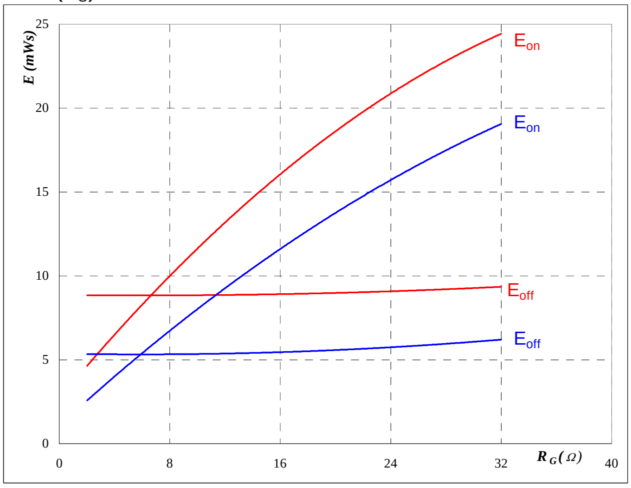
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

Figure 6 Output inverter IGBT

Typical switching energy losses as a function of gate resistor

$E = f(R_G)$



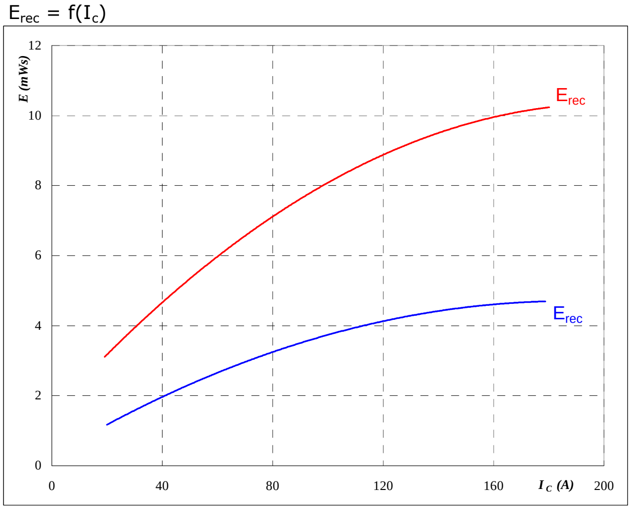
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	100	A

Figure 7 Output inverter IGBT

Typical reverse recovery energy loss as a function of collector current

$E_{rec} = f(I_c)$



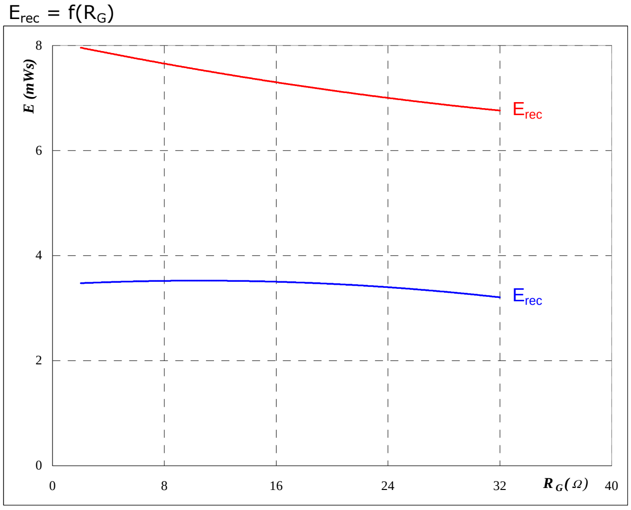
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

Figure 8 Output inverter IGBT

Typical reverse recovery energy loss as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

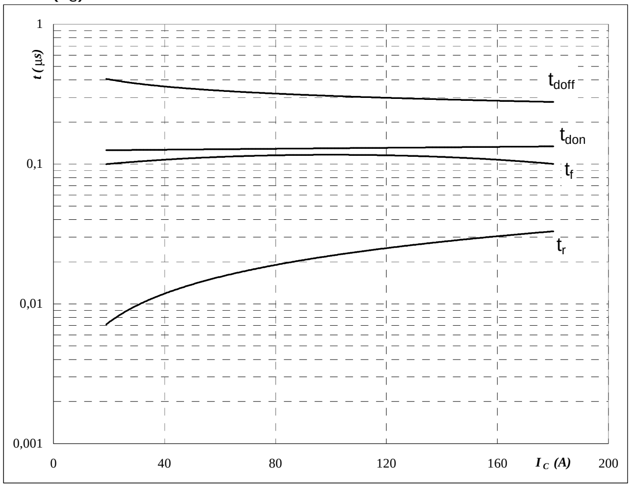
T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	100	A

Output Inverter

Figure 9 Output inverter IGBT

Typical switching times as a function of collector current

t = f(I_C)



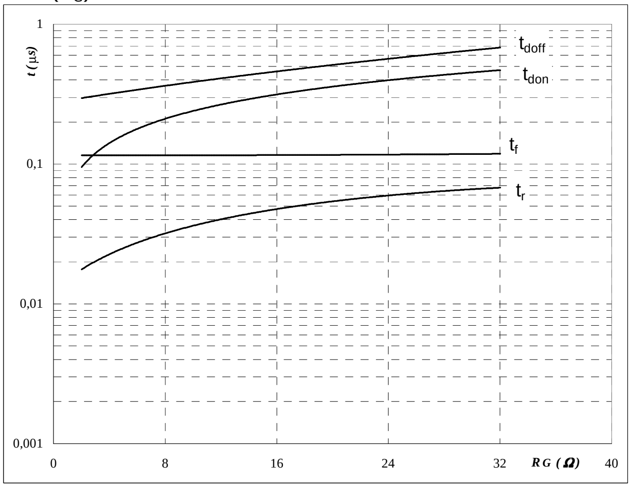
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

Figure 10 Output inverter IGBT

Typical switching times as a function of gate resistor

t = f(R_G)



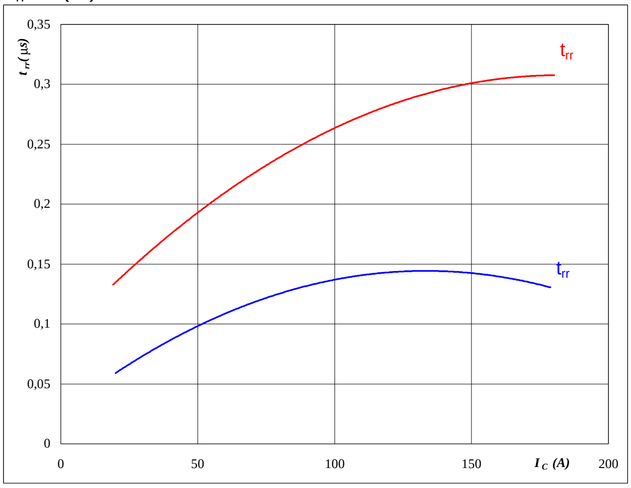
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	100	A

Figure 11 Output inverter FWD

Typical reverse recovery time as a function of collector current

t_{rr} = f(Ic)



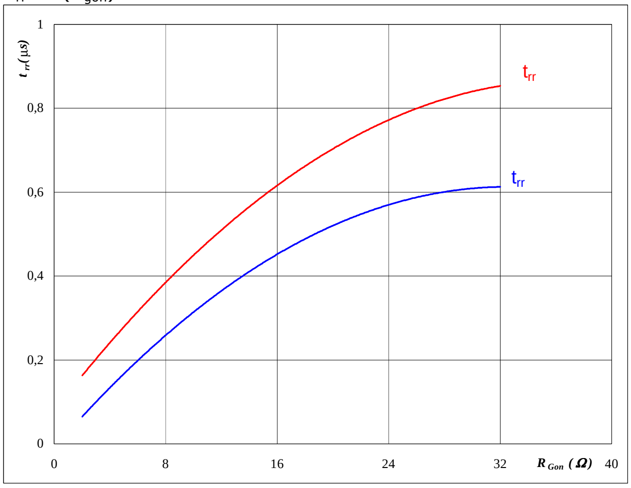
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

Figure 12 Output inverter FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



At

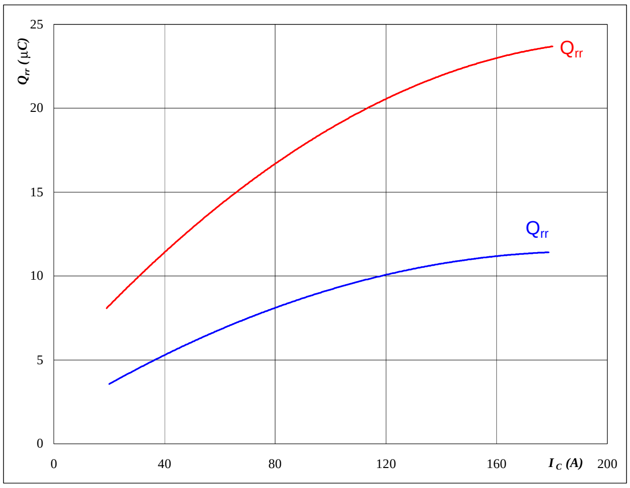
T_j =	25/150	°C
V_R =	600	V
I_F =	100	A
V_{GE} =	±15	V

Output Inverter

Figure 13 Output inverter FWD

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



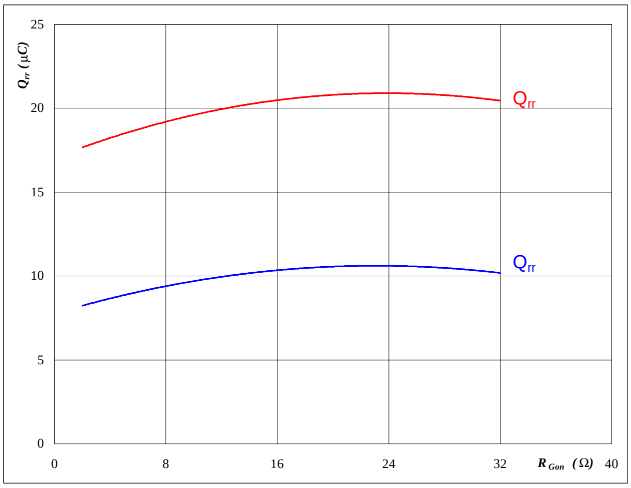
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

Figure 14 Output inverter FWD

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



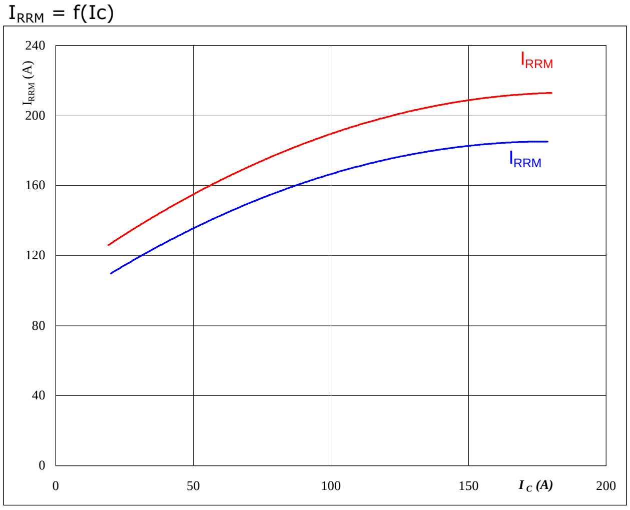
At

T_j =	25/150	°C
V_R =	600	V
I_F =	100	A
V_{GE} =	±15	V

Figure 15 Output inverter FWD

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



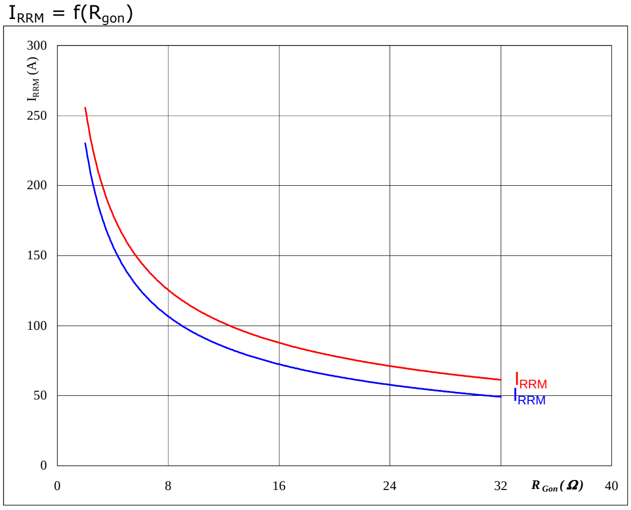
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

Figure 16 Output inverter FWD

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

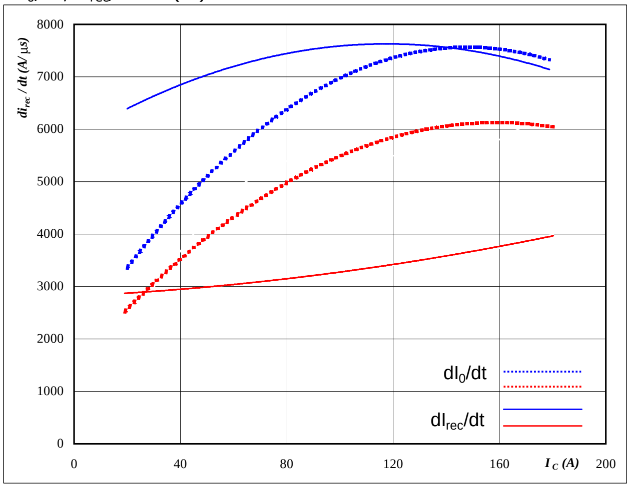
T_j =	25/150	°C
V_R =	600	V
I_F =	100	A
V_{GE} =	±15	V

Output Inverter

Figure 17 Output inverter FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(I_c)$



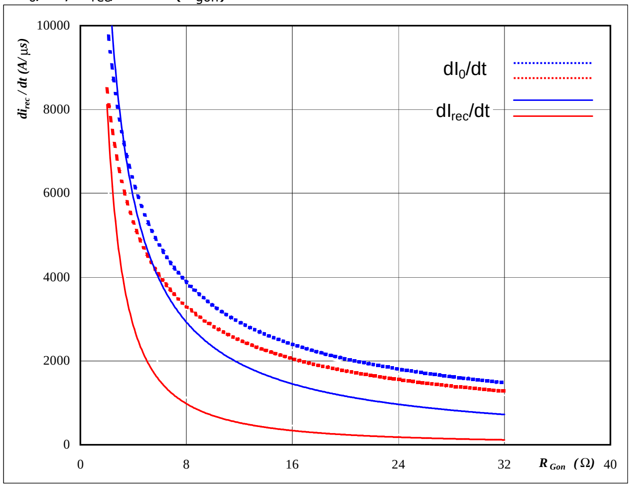
At

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

Figure 18 Output inverter FWD

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



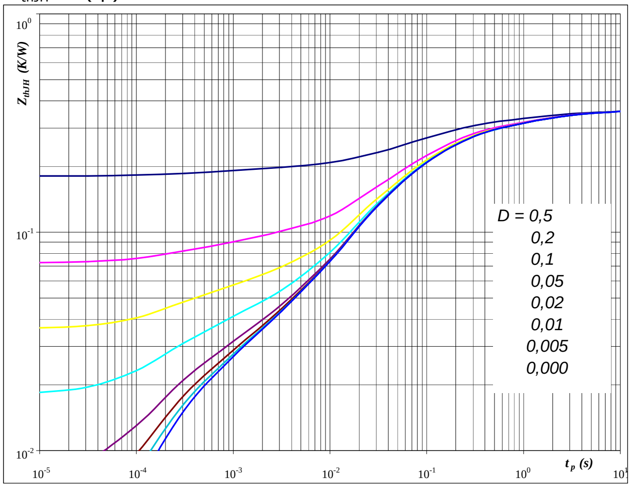
At

T_j =	25/150	°C
V_R =	600	V
I_F =	100	A
V_{GE} =	±15	V

Figure 19

IGBT transient thermal impedance as a function of pulse width

$Z_{thJH} = f(tp)$



At

D =	tp / T				
R_{thJH} =	0,36	K/W	R_{thJH} =	0,44	K/W
Single device heated			All devices heated		

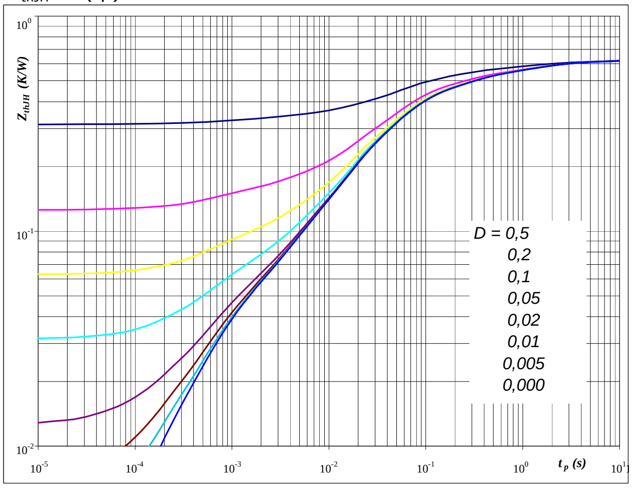
IGBT thermal model values

R (K/W)	Tau (s)	R (K/W)	Tau (s)
0,03	5,4E+00	0,11	5,36
0,06	1,1E+00	0,06	1,05
0,14	1,4E-01	0,14	0,14
0,10	2,6E-02	0,10	0,03
0,02	1,7E-03	0,02	0,00
0,02	2,4E-04	0,02	0,00

Figure 20

FWD transient thermal impedance as a function of pulse width

$Z_{thJH} = f(tp)$



At

D =	tp / T				
R_{thJH} =	0,63	K/W	R_{thJH} =	0,63	K/W
Single device heated			All devices heated		

FWD thermal model values

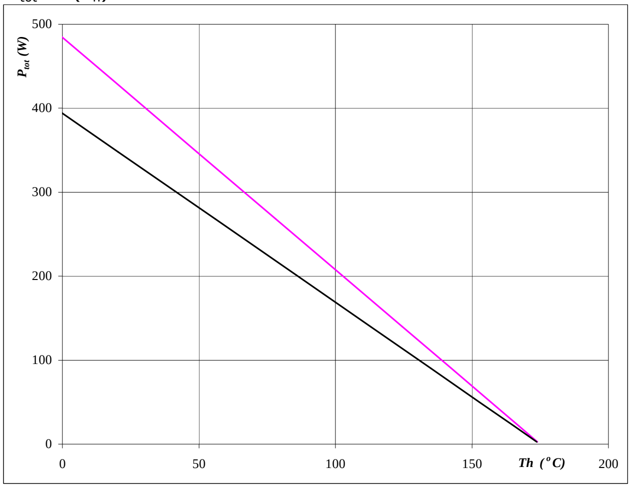
R (K/W)	Tau (s)	R (K/W)	Tau (s)
0,02	9,9E+00	0,02	9,88
0,09	1,4E+00	0,09	1,39
0,13	2,3E-01	0,13	0,23
0,27	4,5E-02	0,27	0,04
0,07	1,1E-02	0,07	0,01
0,04	7,6E-04	0,04	0,00

Output Inverter

Figure 21 Output inverter IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



At

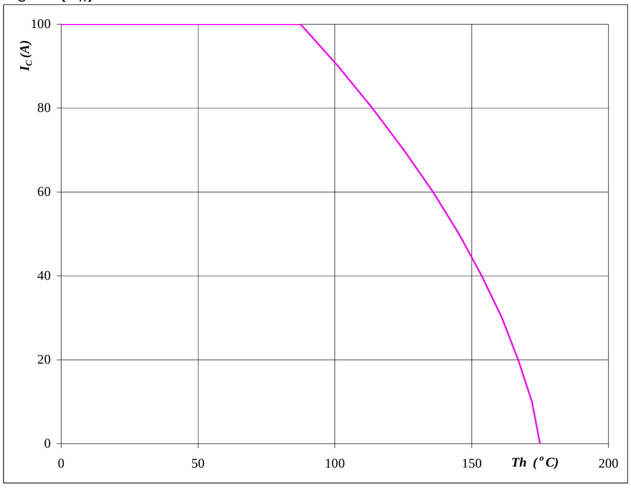
T_j = 175 °C

single heating
overall heating

Figure 22 Output inverter IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$



At

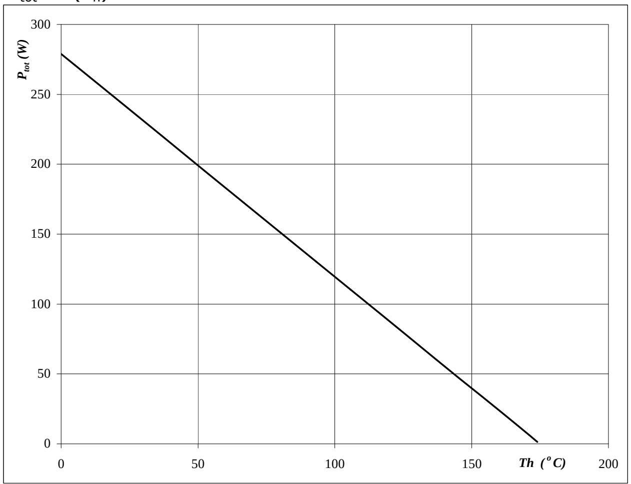
T_j = 175 °C

V_{GE} = 15 V

Figure 23 Output inverter FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



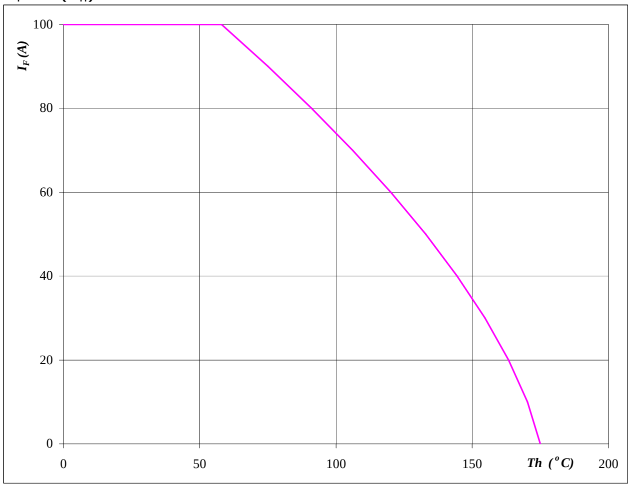
At

T_j = 175 °C

Figure 24 Output inverter FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

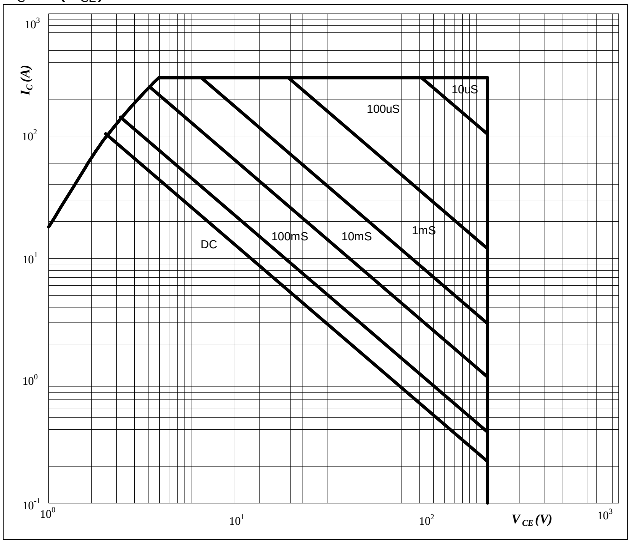
T_j = 175 °C

Output Inverter

Figure 25 Output inverter IGBT

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



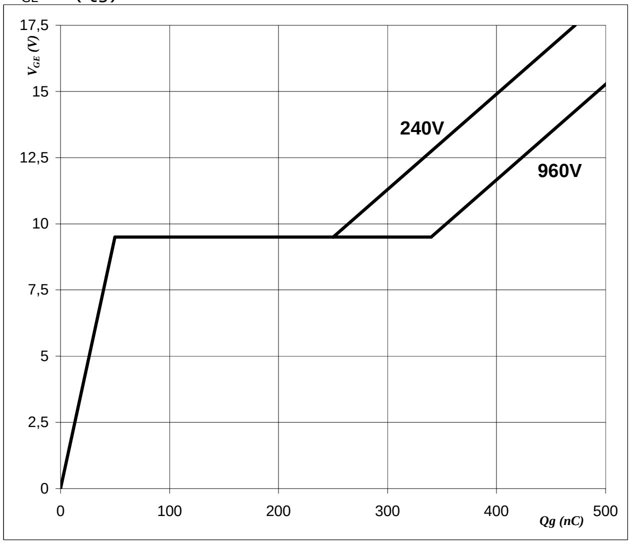
At

D =	single pulse	
Th =	80	ºC
V_{GE} =	±15	V
Tj =	T_{jmax}	ºC

Figure 26 Output inverter IGBT

Gate voltage vs Gate charge

$V_{GE} = f(Qg)$



At

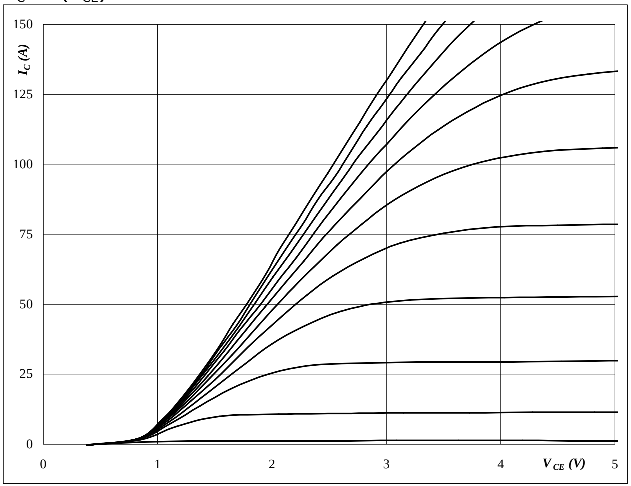
I_C =	100	A

Brake

Figure 1 Brake IGBT

Typical output characteristics

$I_C = f(V_{CE})$



At

t_p = 250 µs

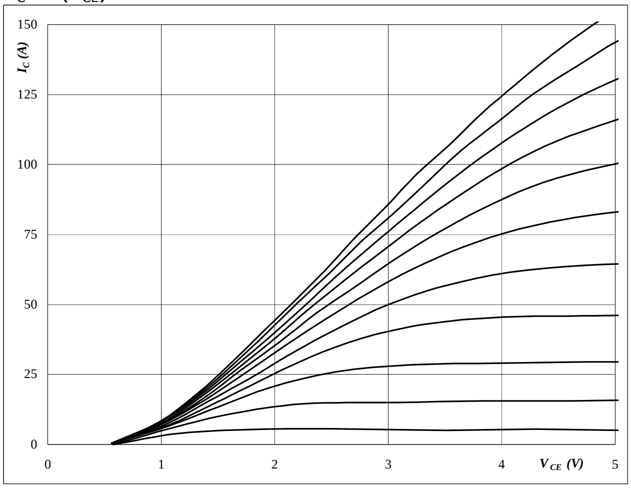
T_j = 25 °C

VGE from 7 V to 17 V in steps of 1 V

Figure 2 Brake IGBT

Typical output characteristics

$I_C = f(V_{CE})$



At

t_p = 250 µs

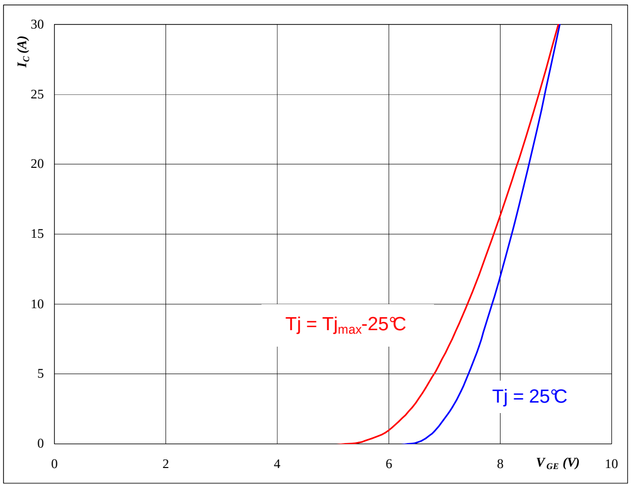
T_j = 150 °C

VGE from 7 V to 17 V in steps of 1 V

Figure 3 Brake IGBT

Typical transfer characteristics

$I_C = f(V_{GE})$



At

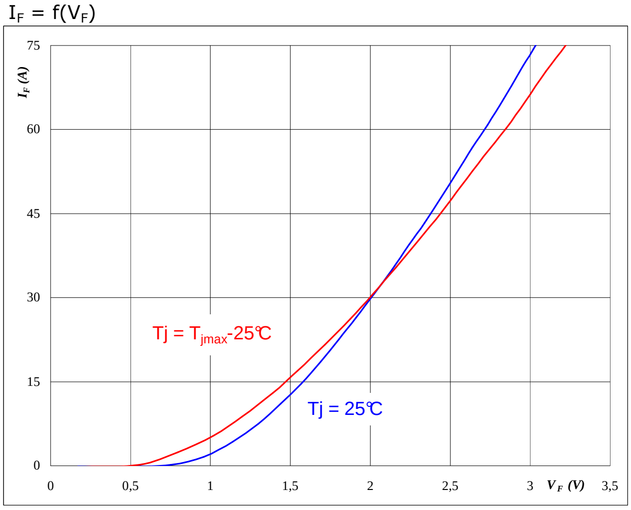
t_p = 250 µs

V_{CE} = 10 V

Figure 4 Brake FWD

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

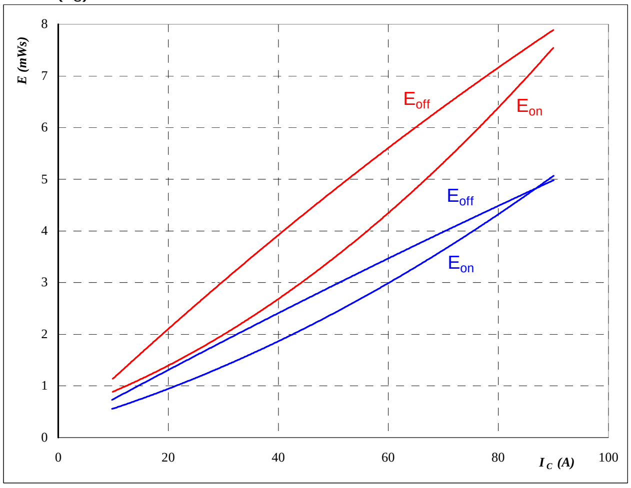
t_p = 250 µs

Brake

Figure 5 Brake IGBT

Typical switching energy losses as a function of collector current

E = f(I_C)



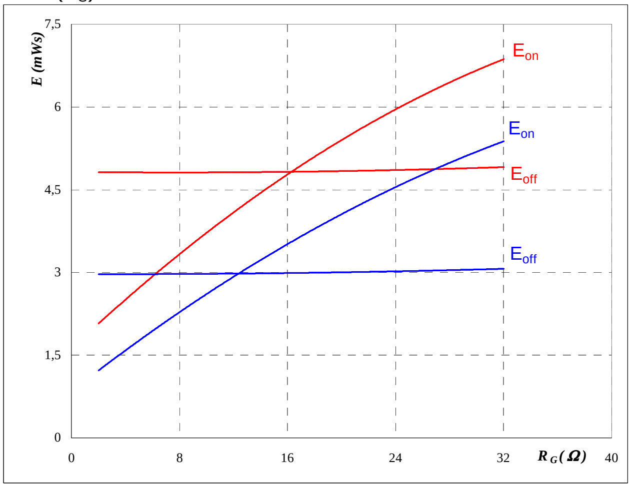
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

Figure 6 Brake IGBT

Typical switching energy losses as a function of gate resistor

E = f(R_G)



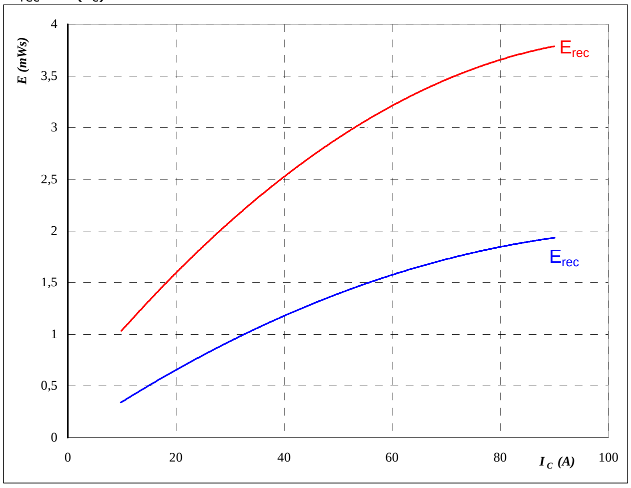
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	50	A

Figure 7 Brake IGBT

Typical reverse recovery energy loss as a function of collector current

E_{rec} = f(I_c)



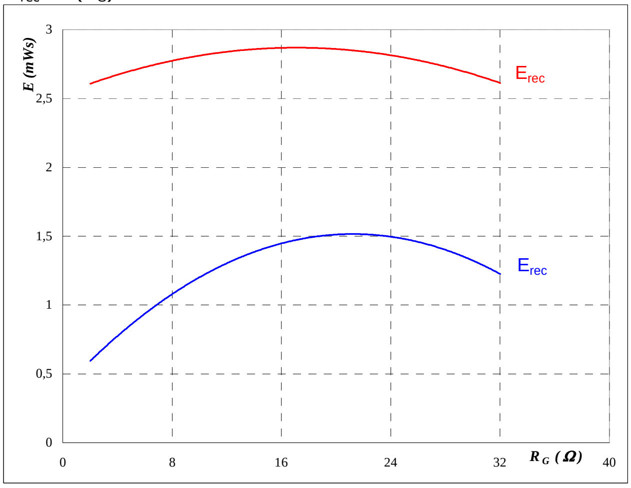
With an inductive load at

T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	8	Ω

Figure 8 Brake IGBT

Typical reverse recovery energy loss as a function of gate resistor

E_{rec} = f(R_G)



With an inductive load at

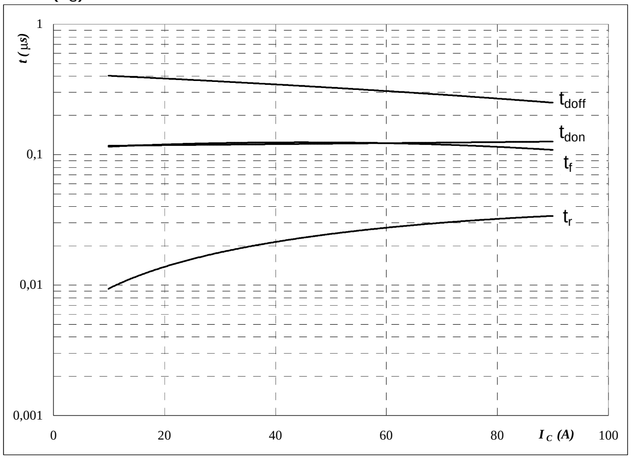
T_j =	25/150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	50	A

Brake

Figure 9 Brake IGBT

Typical switching times as a function of collector current

t = f(I_C)



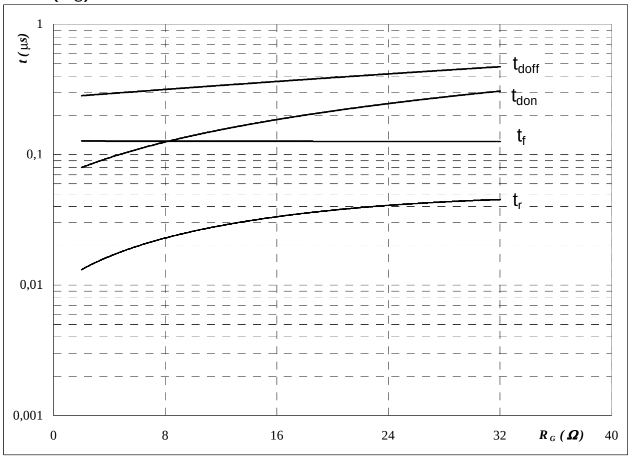
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

Figure 10 Brake IGBT

Typical switching times as a function of gate resistor

t = f(R_G)



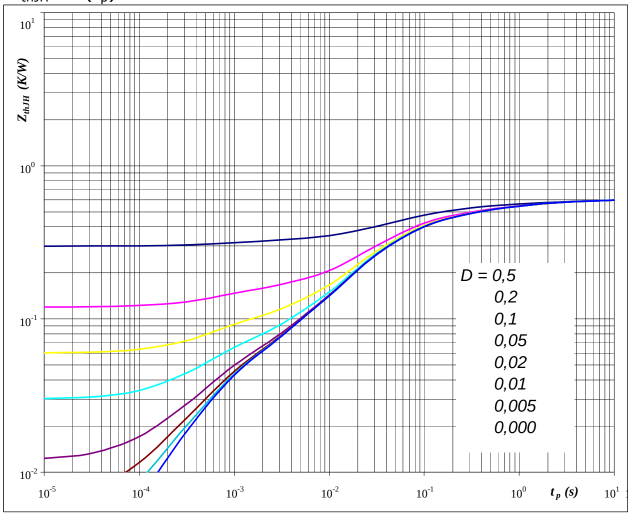
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	50	A

Figure 11 Brake IGBT

IGBT transient thermal impedance as a function of pulse width

Z_{thJH} = f(t_p)



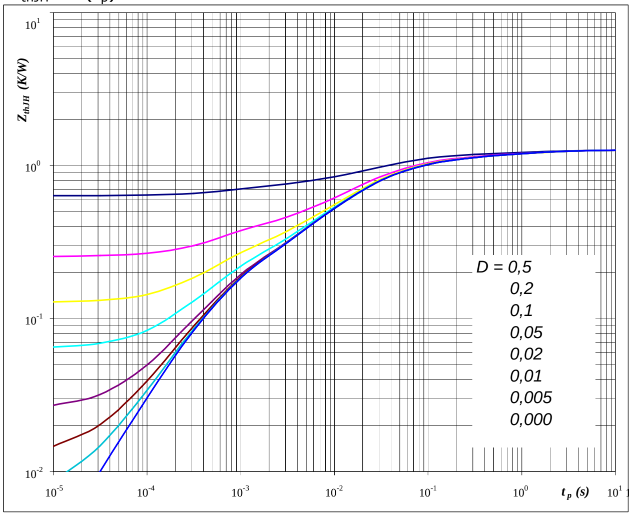
At

D =	tp / T	
R_{thJH} =	0,60	K/W

Figure 12 Brake FWD

FWD transient thermal impedance as a function of pulse width

Z_{thJH} = f(t_p)



At

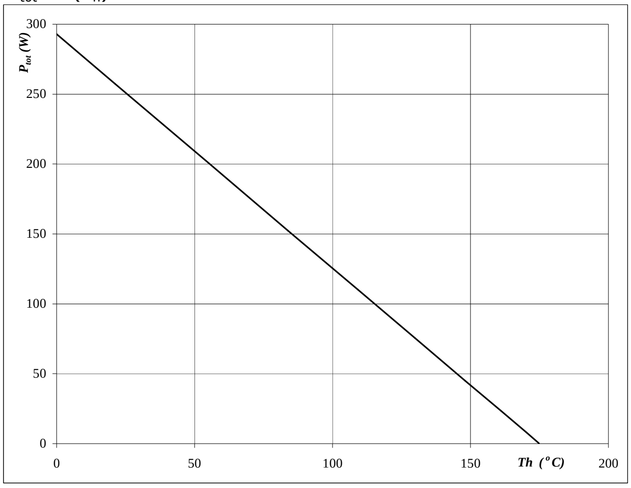
D =	tp / T	
R_{thJH} =	1,27	K/W

Brake

Figure 13	Brake IGBT

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



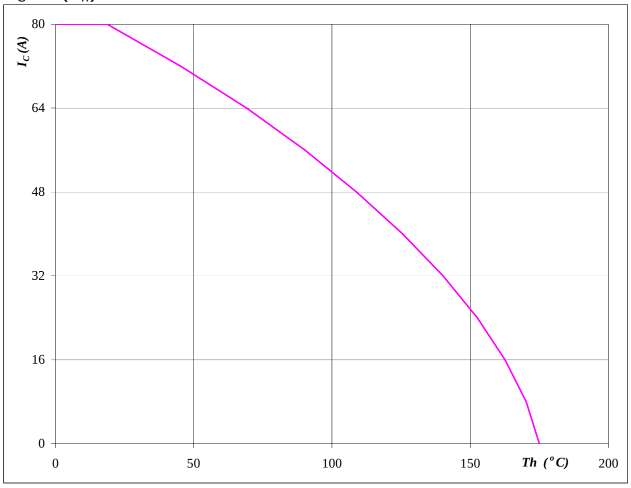
At

T_j = 175 ºC

Figure 14	Brake IGBT

Collector current as a function of heatsink temperature

$I_C = f(T_h)$



At

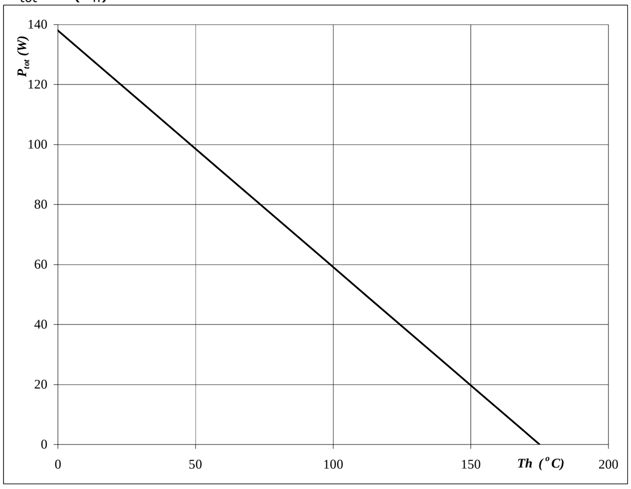
T_j = 175 ºC

V_{GE} = 15 V

Figure 15	Brake FWD

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



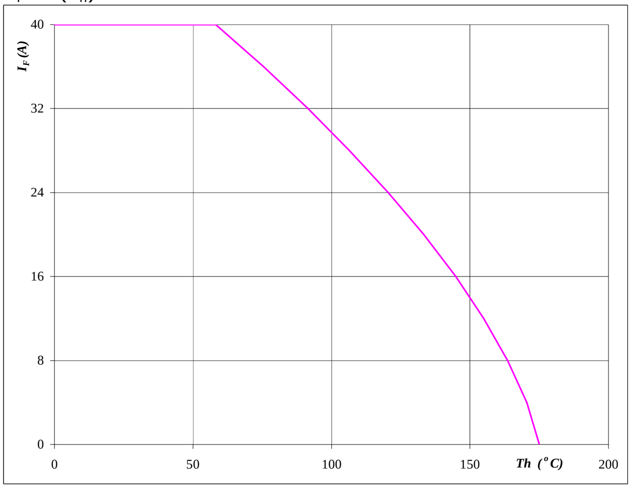
At

T_j = 175 ºC

Figure 16	Brake FWD

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

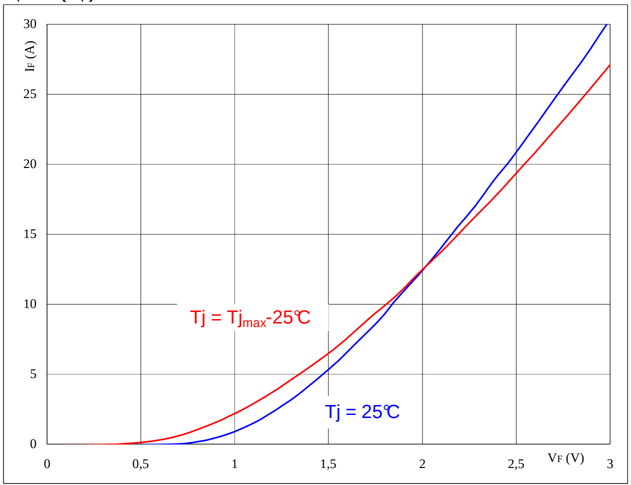
T_j = 175 ºC

Brake Inverse Diode

Figure 1	Brake inverse diode

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



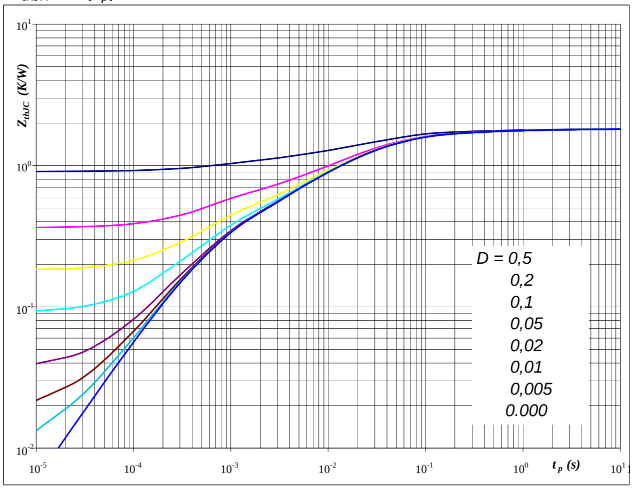
At

t_p =	250	μs

Figure 2	Brake inverse diode

Diode transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



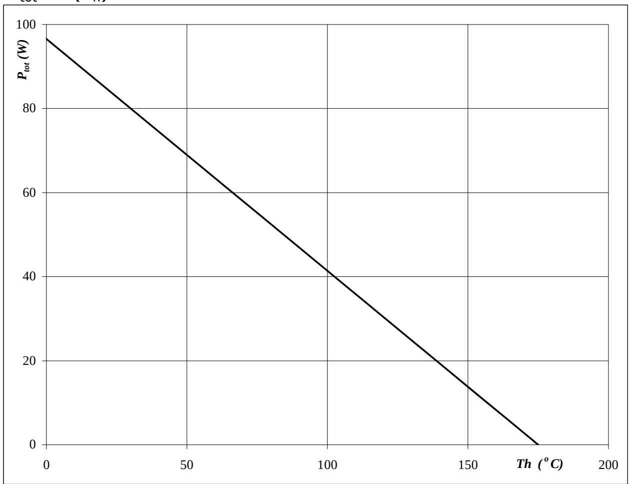
At

D =	tp / T	
R_{thJH} =	1,81	K/W

Figure 3	Brake inverse diode

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



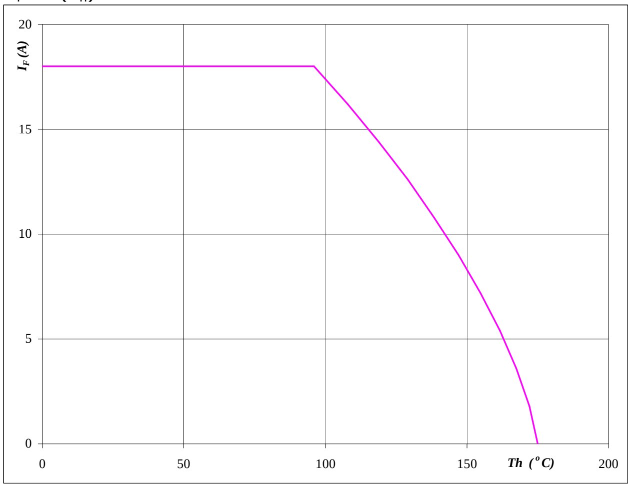
At

T_j =	175	ºC

Figure 4	Brake inverse diode

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



At

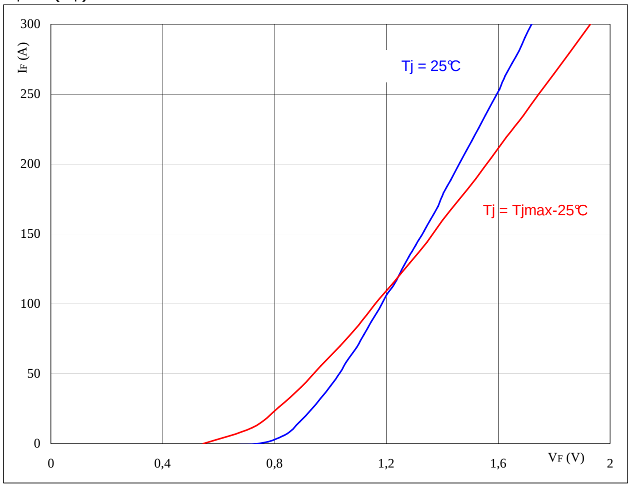
T_j =	175	ºC

Input Rectifier Bridge

Figure 1 Rectifier diode

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



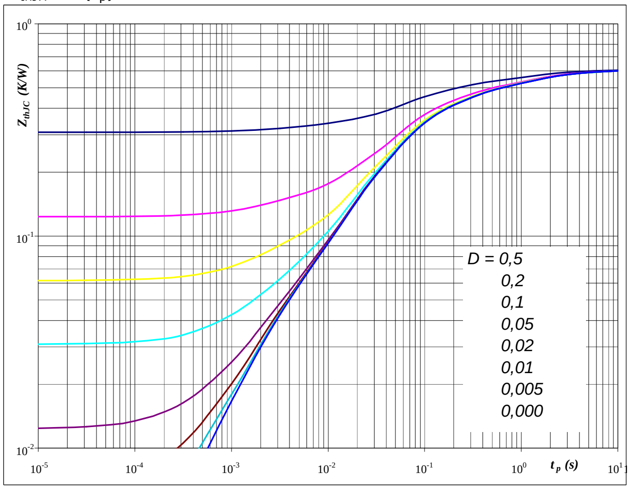
At

t_p = 250 µs

Figure 2 Rectifier diode

Diode transient thermal impedance as a function of pulse width

$Z_{thJH} = f(t_p)$



At

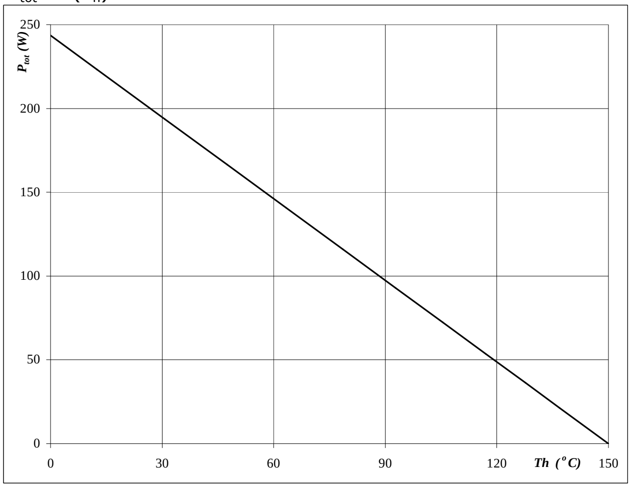
D = tp / T

R_{thJH} = 0,62 K/W

Figure 3 Rectifier diode

Power dissipation as a function of heatsink temperature

$P_{tot} = f(T_h)$



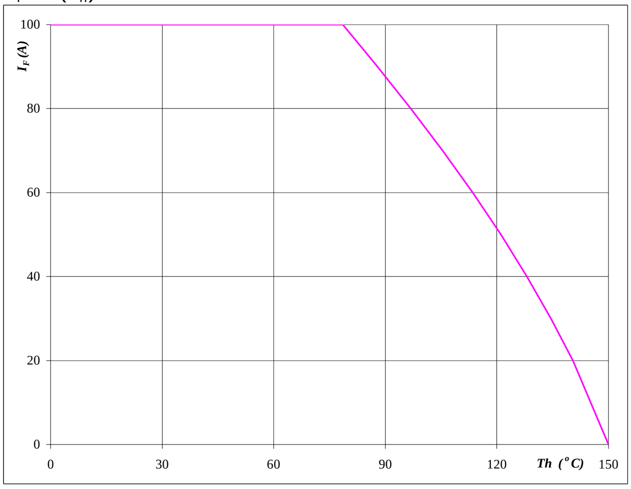
At

T_j = 150 ºC

Figure 4 Rectifier diode

Forward current as a function of heatsink temperature

$I_F = f(T_h)$



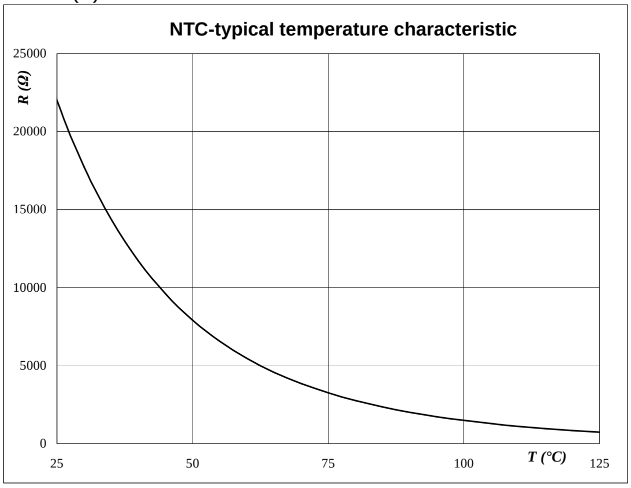
At

T_j = 150 ºC

Thermistor

Figure 1 Thermistor

Typical NTC characteristic
as a function of temperature
$R_T = f(T)$



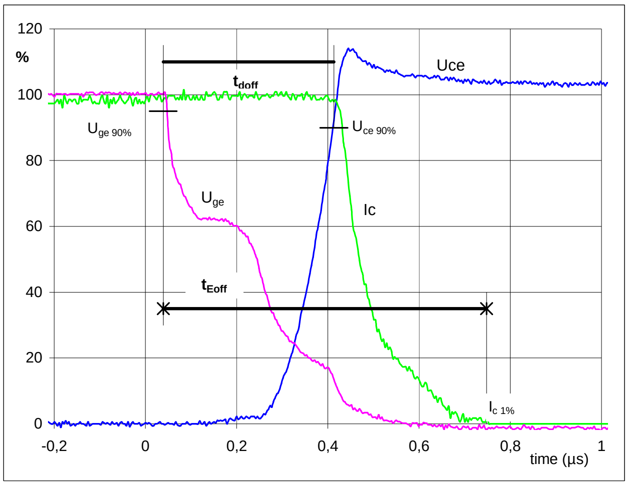
Switching Definitions Output Inverter

General conditions

T_j	=	150 °C
R_{gon}	=	8 Ω
R_{goff}	=	8 Ω

Figure 1 Output inverter IGBT

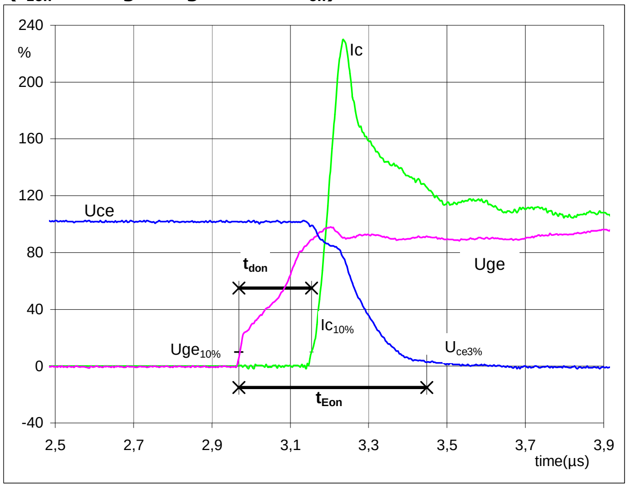
Turn-off Switching Waveforms & definition of tdoff, t_{Eoff}
(t_{Eoff} = integrating time for E_{off})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	100	A
t_{doff} =	0,36	µs
t_{Eoff} =	0,71	µs

Figure 2 Output inverter IGBT

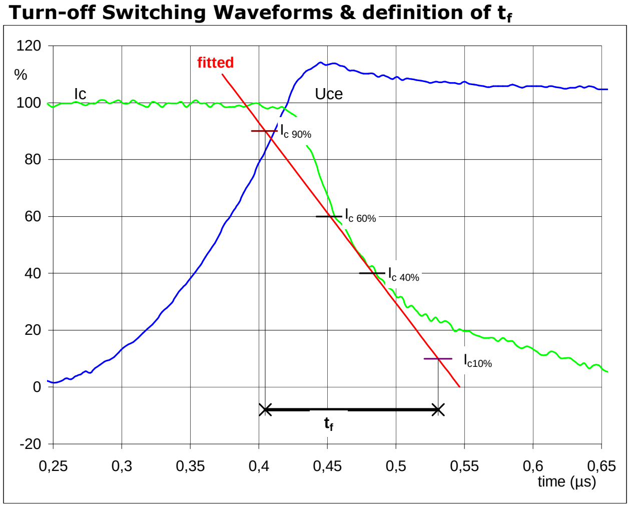
Turn-on Switching Waveforms & definition of tdon, t_{Eon}
(t_{Eon} = integrating time for E_{on})



V_{GE} (0%) =	-15	V
V_{GE} (100%) =	15	V
V_C (100%) =	600	V
I_C (100%) =	100	A
t_{don} =	0,18	µs
t_{Eon} =	0,48	µs

Figure 3 Output inverter IGBT

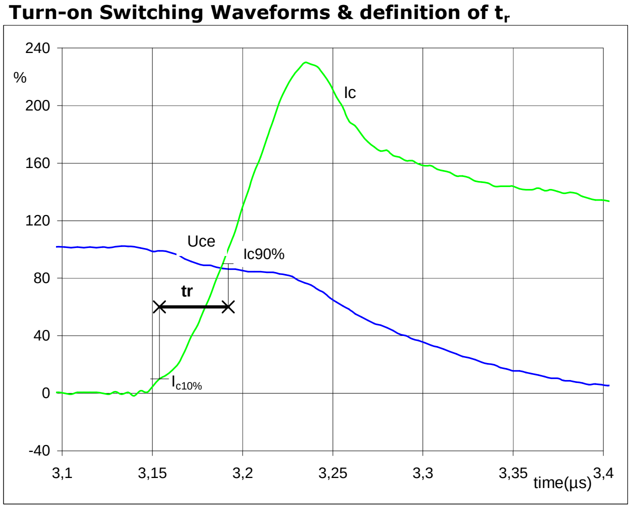
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	600	V
I_C (100%) =	100	A
t_f =	0,11	µs

Figure 4 Output inverter IGBT

Turn-on Switching Waveforms & definition of t_r

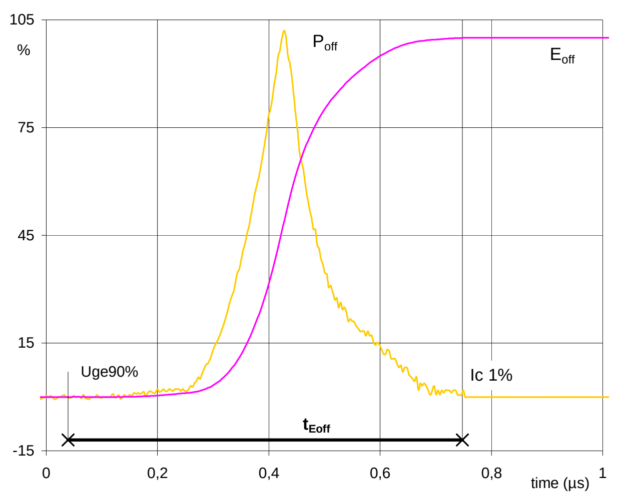


V_C (100%) =	600	V
I_C (100%) =	100	A
t_r =	0,04	µs

Switching Definitions Output Inverter

Figure 5 Output inverter IGBT

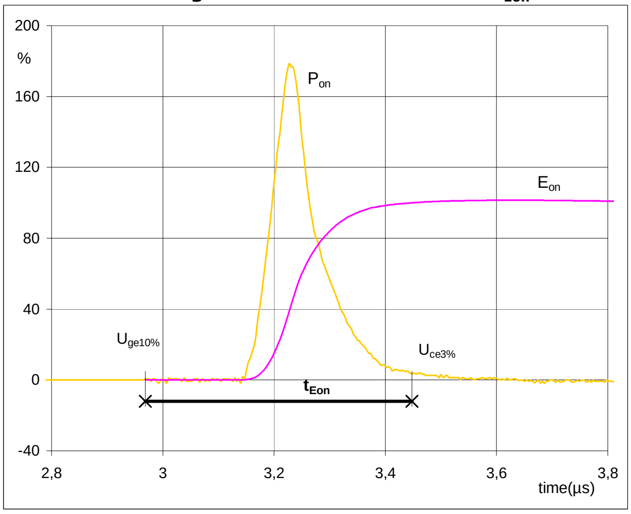
Turn-off Switching Waveforms & definition of t_{Eoff}



P_{off} (100%) =	59,90	kW
E_{off} (100%) =	8,77	mJ
t_{Eoff} =	0,71	µs

Figure 6 Output inverter IGBT

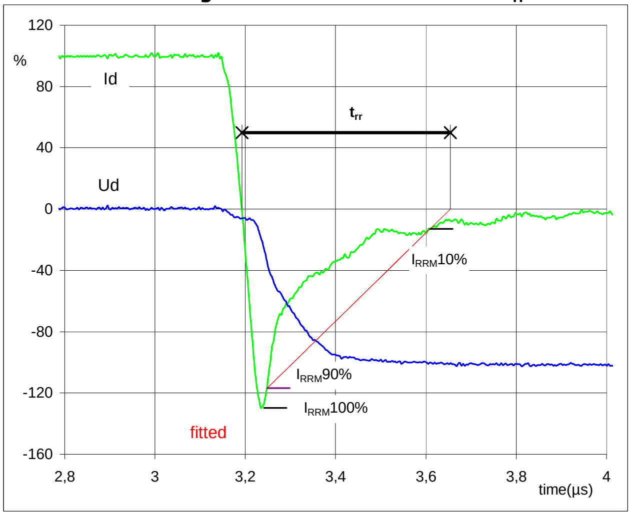
Turn-on Switching Waveforms & definition of t_{Eon}



P_{on} (100%) =	59,90	kW
E_{on} (100%) =	10,51	mJ
t_{Eon} =	0,48	µs

Figure 7 Output inverter FWD

Turn-off Switching Waveforms & definition of t_{rr}

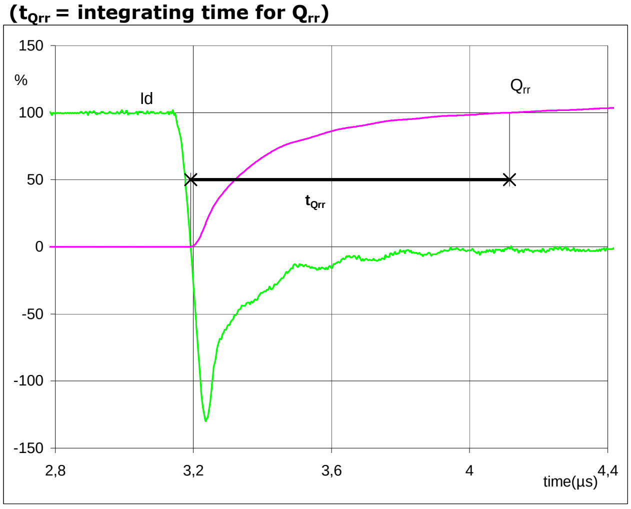


V_d (100%) =	600	V
I_d (100%) =	100	A
I_{RRM} (100%) =	-129	A
t_{rr} =	0,34	µs

Switching Definitions Output Inverter

Figure 8 Output inverter FWD

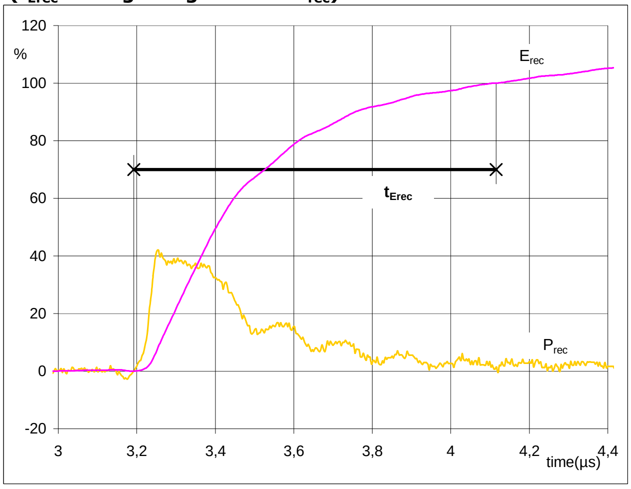
Turn-on Switching Waveforms & definition of t_{Qrr}
(t_{Qrr} = integrating time for Q_{rr})



I_d (100%) =	100	A
Q_{rr} (100%) =	19,13	µC
t_{Qint} =	0,92	µs

Figure 9 Output inverter FWD

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})



P_{rec} (100%) =	59,90	kW
E_{rec} (100%) =	7,39	mJ
t_{Erec} =	0,92	µs

Ordering Code and Marking - Outline - Pinout

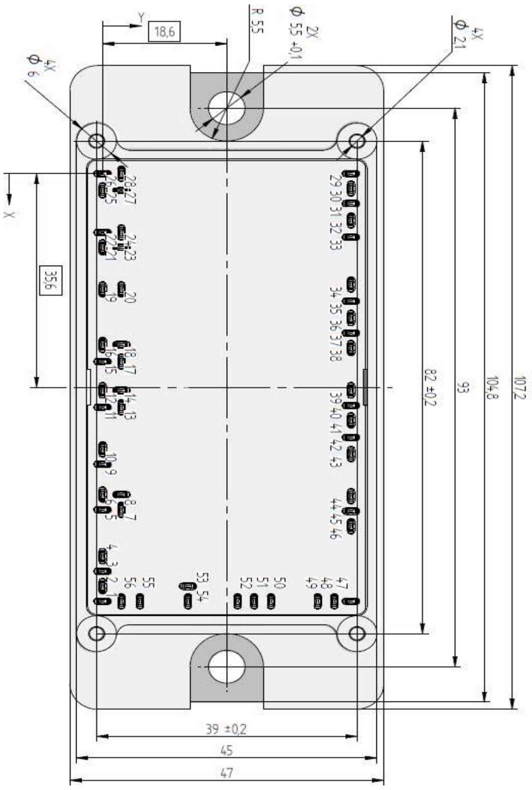
Ordering Code & Marking

Version	Ordering Code	in DataMatrix as	in packaging barcode as
without thermal paste with solder pins	V23990-P760-A-PM	P760-A	P760-A
with thermal paste and solder pins	V23990-P760-A-/3/-PM	P760-A	P760-A-/3/
without thermal paste with Press-fit pins	V23990-P760-AY-PM	P760-AY	P760-AY
with thermal paste and Press-fit pins	V23990-P760-AY-/3/-PM	P760-AY	P760-AY-/3/

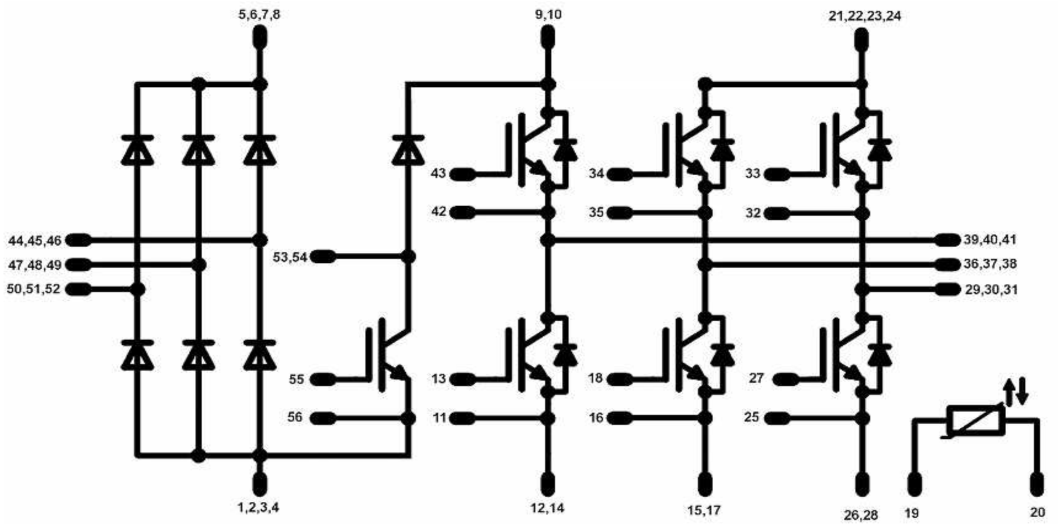
Outline

Pin table

Pin		X	Y	Pin		X	Y
1	DC-	71,2	0	33	G	10,6	37,2
2	DC-	68,7	0	34	G	18,45	37,2
3	DC-	66,2	0	35	E	21,25	37,2
4	DC-	63,7	0	36	V	24,05	37,2
5	DC+	55,95	0	37	V	26,55	37,2
6	DC+	53,45	0	38	V	29,05	37,2
7	DC+	55,95	2,8	39	W	36,1	37,2
8	DC+	53,45	2,8	40	W	38,6	37,2
9	DC+	48,4	0	41	W	41,1	37,2
10	DC+	45,9	0	42	E	43,9	37,2
11	E	38,9	0	43	G	46,7	37,2
12	DC-	36,1	0	44	L1	53,7	37,2
13	G	38,9	2,8	45	L1	56,2	37,2
14	DC-	36,1	2,8	46	L1	58,7	37,2
15	DC-	31,3	0	47	L2	71,2	37,2
16	E	28,5	0	48	L2	71,2	34,7
17	DC-	31,3	2,8	49	L2	71,2	32,2
18	G	28,5	2,8	50	L3	71,2	25,2
19	R2	19,3	0	51	L3	71,2	22,7
20	R1	19,3	2,8	52	L3	71,2	20,2
21	DC+	12,3	0	53	BrC	71,2	12,8
22	DC+	9,8	0	54	BrC	68,7	12,8
23	DC+	12,3	2,8	55	BrG	71,2	5,6
24	DC+	9,8	2,8	56	BrE	71,2	2,8
25	E	2,8	0				
26	DC-	0	0				
27	G	2,8	2,8				
28	DC-	0	2,8				
29	U	0	37,2				
30	U	2,5	37,2				
31	U	5	37,2				
32	E	7,8	37,2				



Pinout



DISCLAIMER

The information given in this datasheet describes the type of component and does not represent assured characteristics. For tested values please contact Vincotech.Vincotech reserves the right to make changes without further notice to any products herein to improve reliability, function or design. Vincotech does not assume any liability arising out of the application or use of any product or circuit described herein; neither does it convey any license under its patent rights, nor the rights of others.

LIFE SUPPORT POLICY

Vincotech products are not authorised for use as critical components in life support devices or systems without the express written approval of Vincotech.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in labelling can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.